

to 4 or a polyamic acid resin which is a precursor of said polyimide resin.

6. The resin composition according to claim 5, comprising a methylol compound.

7. The resin composition according to claim 6, wherein the content of said methylol compound is 0.1 to 20% by mass with respect to said polyimide resin or said polyamic acid resin which is a precursor of said polyimide resin.

8. A cured film obtained by curing the resin composition according to any one of claims 5 to 7.

9. A laminated film in which the resin composition according to any one of claims 5 to 7 is laminated on at least one side of a heat-resistant insulation film.

10. The laminated film according to claim 9, wherein a release treatment is performed on the surface of said heat-resistant insulation film on which said resin composition is laminated.

11. The laminated film according to claim 9 or 10, wherein a release-treated film is further laminated on the surface of said resin composition laminated on said heat-resistant insulation film.

12. A method of producing a semiconductor device using the resin composition according to any one of claims 5 to 7.

13. The method of producing a semiconductor device according to claim 12, wherein a substrate for semiconductor circuit formation and a support substrate are joined

together via at least one adhesive resin layer,

said adhesive resin layer is formed using said resin composition, and

said method comprising at least:

the step of thinning said substrate for semiconductor circuit formation;

the step of device-processing said substrate for semiconductor circuit formation; and

the step of peeling off said substrate for semiconductor circuit formation from said

support substrate.

14. A method of producing a semiconductor device using the laminated film according to any one of claims 9 to 11.

15. The method of producing a semiconductor device according to claim 14, wherein a substrate for semiconductor circuit formation and a support substrate are joined

together via at least one adhesive resin layer,

said adhesive resin layer is formed using said laminated film, and

said method comprising at least:

the step of thinning said substrate for semiconductor circuit formation;

the step of device-processing said substrate for semiconductor circuit formation; and

the step of peeling off said substrate for semiconductor circuit formation from said

support substrate.